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The present invention provides a method for fabricating low-resistance, sub-0.1 μm channel T-gate MOSFETs that do not exhibit any poly depletion problems. The inventive method employs a damascene-gate processing step and a chemical oxide removal etch to fabricate such MOSFETs. The chemical oxide removal may be performed in a vapor containing HF and NH_3 or a plasma containing HF and NH_3 .

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